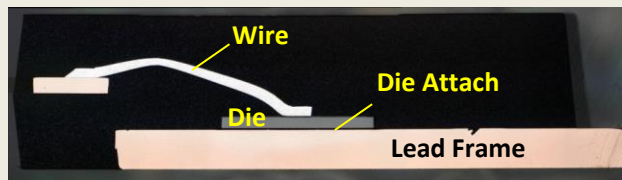


## ST Micro electronics SCT30N120 SiC POWER PACKAGE ANALYSIS REPORT

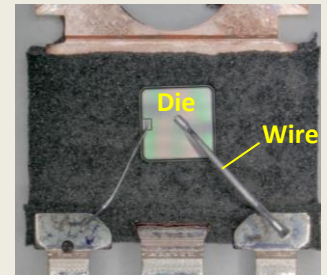
**July,5 2016.** This is a detailed package analysis report of the SCT30N120 SiC Power device. This product realizes the continuous operation at 200°C.



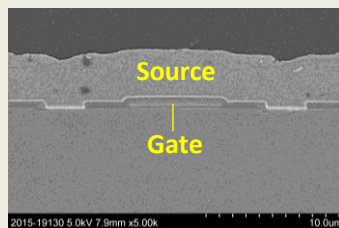
Package



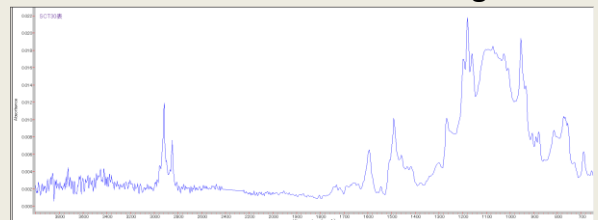
Package Cross section



Die Image



Die Cross section



Package Material Analysis(FT-IR)

The packaging technologies are key for realizing high temperature continuous operation. Packaging key technologies to realize 200°C continuous operation are highlighted in this report by comparing 4 products as below. Detail analysis of surface treatment of power devices, die attachment, wire bonding and materials are conducted in 35 pages report.

- ✓ **SiC device : STMicro SCT30N120 (1200V) Tjmax=200°C**
- ✓ SiC device : ROHM SCH2080KE (1200V) Tjmax=175°C
- ✓ Silicon device: STMicro STGW40V60DLF (600V IGBT) Tjmax=175°C
- ✓ Silicon device: Infineon SPI21N10 (100V MOSFET) Tjmax=175°C

**Priced to sell at \$3,500**

**Contact LTEC Corporation**

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15G-0003-1

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